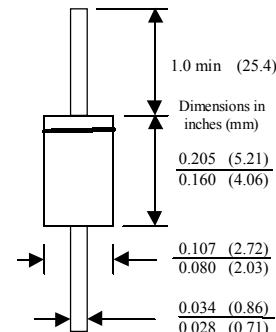


1N5817 - 1N5819

Features

- 1.0 ampere operation at $T_A = 90^\circ\text{C}$ with no thermal runaway.
- For use in low voltage, high frequency inverters free wheeling, and polarity protection applications.



1.0 Ampere Schottky Barrier Rectifiers

Absolute Maximum Ratings*

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
I_0	Average Rectified Current .375 " lead length @ $T_A = 90^\circ\text{C}$	1.0	A
$i_f(\text{surge})$	Peak Forward Surge Current 8.3 ms single half-sine-wave Superimposed on rated load (JEDEC method)	25	A
P_D	Total Device Dissipation Derate above 25°C	1.25 12.5	W mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	80	$^\circ\text{C}/\text{W}$
T_{stg}	Storage Temperature Range	-65 to +125	$^\circ\text{C}$
T_J	Operating Junction Temperature	-65 to +125	$^\circ\text{C}$

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Parameter	Device			Units
	1N5817	1N5818	1N5819	
Peak Repetitive Reverse Voltage	20	30	40	V
Maximum RMS Voltage	14	21	28	V
DC Reverse Voltage (Rated V_R)	20	30	40	V
Maximum Reverse Current	$T_A = 25^\circ\text{C}$			mA
$@ \text{rated } V_R$		0.5		mA
$T_A = 100^\circ\text{C}$		10		mA
Maximum Forward Voltage	@ 1.0 A		450	mV
@ 3.0 A		750	875	mV
Typical Junction Capacitance	$V_R = 4.0 \text{ V}, f = 1.0 \text{ MHz}$			pF
	110			

Schottky Barrier Rectifiers (continued)

Typical Characteristics

